2N3669 2N3670

SILICON CONTROLLED RECITIFIERS 16 AMP, 400 THRU 600 VOLT



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3669 and 2N3670 are hermetically sealed SCRs designed for sensing circuit applications and control systems. Higher voltage devices and electrical selections are available on special order.

MARKING: FULL PART NUMBER



MAXIMUM RATINGS: (T_C=25°C unless otherwise noted)

	SYMBOL	<u>2N3669</u>	<u>2N3670</u>	UNITS
Peak Repetitive Off-State Voltage	V_{RRM}	200	400	V
Peak Repetitive Off-State Voltage	V_{DRM}	400	600	V
RMS On-State Current (T _C =90°C)	I _{T(RMS)}	16		Α
Peak One Cycle Surge Current (60Hz, T _C =80°C)	ITSM	200		Α
Peak Gate Current	I _{GM}	4.0		Α
Average Gate Power Dissipation	P _{G(AV)}	0.5		W
Operating and Storage Junction Temperature	T _J , T _{stg}	-40 to +125		°C
Thermal Resistance	ΘJC	1.7		°C/W

ELECTRICAL CHARACTERISTICS: (T_C=25°C unless otherwise noted)

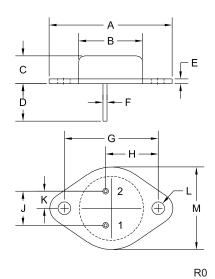
SYMBOL	TEST CONDITIONS	MIN	ΤΫ́Ρ	MAX	UNITS
IRRM	V _R =Rated V _{RRM} , T _C =100°C			1.0	mA
I _{DRM}	V _D =Rated V _{DRM} , T _C =100°C			2.0	mA
I _{GT}	V _D =7.0V	1.0		40	mA
I_{H}	$R_G=1.0K\Omega$	0.5		50	mA
V_{TM}	I _T =25A			1.8	V
V_{GT}	V _D =7.0V			2.0	V
dv/dt	$V_D = \frac{2}{3} V_{DRM}, R_G = 1.0 k\Omega, T_C = 100 ^{\circ} C$	10	400		V/µs
^t gd	I _G =125mA, diG/dt=1.25A/μs			500	ns
t_q	$V_D = \frac{2}{3} V_{DRM}$, $V_R = 35V$, $I_T = 10A$, $T_C = 90$ °C			50	μs

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TO-3 50 MIL CASE - MECHANICAL OUTLINE



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	1.516	1.573	38.50	39.96			
B (DIA)	0.748	0.875	19.00	22.23			
С	0.250	0.450	6.35	11.43			
D	0.433	0.516	11.00	13.10			
Е	0.054	0.065	1.38	1.65			
F	0.048	0.051	1.22	1.30			
G	1.177	1.197	29.90	30.40			
Н	0.650	0.681	16.50	17.30			
J	0.420	0.440	10.67	11.18			
K	0.205	0.225	5.21	5.72			
L (DIA)	0.151	0.172	3.84	4.36			
M	0.984	1.050	25.00	26.67			

TO-3 50 MIL (REV: R0)

LEAD CODE:

- 1) Gate
- 2) Cathode

Case) Anode

MARKING:

FULL PART NUMBER

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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